

April 19, 2011

Santa Clara, CA – The U.S. Patent and Trademark Office granted Multibeam Corporation another key patent. US Patent #7,928,404 was issued to Multibeam on April 19, 2011. The patent covers a method to blank and unblank an electron beam with high speed and low blur, enabling faster and more precise Electron-Beam Lithography (EBL).

Multibeam's all-electrostatic e-beam columns are small, extremely fast and low-cost. Our multi-column architecture scales for high throughput. By complementing optical lithography, Multibeam's Complementary EBL (CEBL) enables the most cost-efficient production of next-generation microchips in high volumes.

Multibeam has 15 patents granted in the United States, as well as a pipeline of patents pending. In addition to its patent portfolio, Multibeam has completed substantial research, development and engineering in high-resolution low-cost e-beam columns, as well as multiple-column architectures.

#### **About Multibeam Corporation**

Multibeam is the technology leader in high-speed multiple-column E-Beam Lithography (EBL). In 2011, Multibeam introduced Complementary EBL (CEBL). CEBL extends Optical Lithography and enables the production of next-generation semiconductors in high volumes at reduced cost. Multibeam is led by Dr. David K. Lam, founder and former CEO of Lam Research Corporation. More information is available at [www.multibeamcorp.com](http://www.multibeamcorp.com).

Contact: Ted Prescop (408) 980-1800 x3 [info@multibeamcorp.com](mailto:info@multibeamcorp.com)